TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2 S A 1 9 3 9

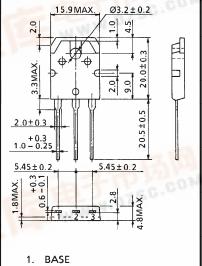
POWER AMPLIFIER APPLICATIONS

查询2SA1939供应商

- Complementary to 2SC5196
- Recommend for 40W High Fidelity Audio Frequency Amplifier Output Stage.

Output Stage.			
MAXIMUM RATINGS (Ta = 25°C)	DZSC.CO		
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	$V_{ m EBO}$	-5	V
Collector Current	$I_{\mathbf{C}}$	-6	A
Base Current	$I_{\mathbf{B}}$	-0.6	A
Collector Power Dissipation (Tc=25°C)	PC	60	W
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$\mathrm{T}_{\mathrm{stg}}$	-55~150	°C

Unit in mm



- 2. COLLECTOR (HEAT SINK)
- **EMITTER**

JEDEC EIAJ TOSHIBA 2-16C1A

Weight: 4.7g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

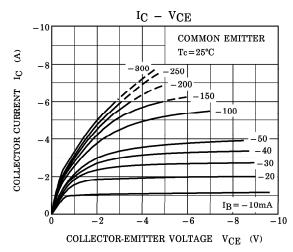
ELECTRICAL CHARACTERISTICS (Ta = 25 C)			-8 ·8 (-7F)			
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -80V, I_{E} = 0$	_	_	-5.0	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_{C} = 0$	_	_	-5.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{C} = -50 \text{mA}, I_{B} = 0$	-80	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{CE} = -5V, I_{C} = -1A$	55	_	160	
	$h_{\mathrm{FE}(2)}$	$V_{CE} = -5V, I_{C} = -3A$	35	80		11773
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = -5A, I_B = -0.5A$	=我	-1.0	-2.0	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE} = -5V$, $I_{C} = -3A$	-W	-0.95	-1.5	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -5V$, $I_C = -1A$	_	30	_	MHz
Collector Output Capacitance	Cob	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	_	180	_	pF

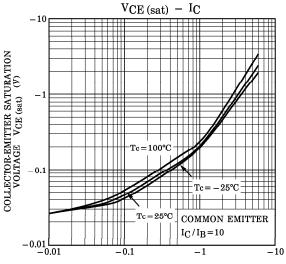
Note: $h_{FE(1)}$ Classification $R: 55\sim110$, $O: 80\sim160$

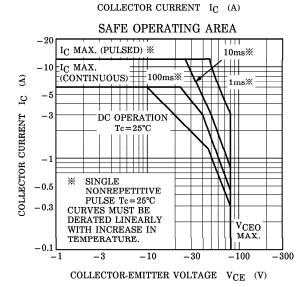
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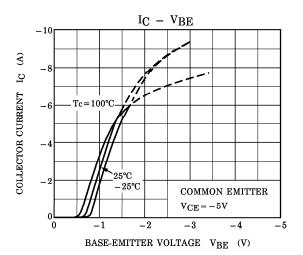
The interpretation contained herein is subject to change without notice.

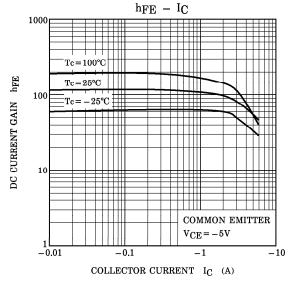
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